1GB – 2x64Mx72 DDR2 SDRAM UNBUFFERED, w/PLL, Mini-DIMM

FEATURES

- Unbuffered 244-pin, dual in-line memory module (Mini-DIMM)
- Fast data transfer rates: PC2-6400*, PCS-5300*, PC2-4200 and PC2-3200
- Utilizes 800*, 667*, 533 and 400 Mb/s DDR2 SDRAM components
- $V_{CC} = V_{CCQ} = 1.8V \pm 0.1V$
- $V_{CCSPD} = 1.7V$ to $3.6V$
- Differential data strobe (DQS, DQS#) option
- Four-bit prefetch architecture
- Programmable CAS# latency (CL): 3, 4, 5* and 6*
- Programmable burst: Length (4, 8)
- On-die termination (ODT)
- Serial Presence Detect (SPD) with EEPROM
- JEDEC Standard 1.8V I/O (SSTK_18 Compatible)
- Gold (Au) edge contacts
- Dual Rank
- RoHS compliant
- Package option
  - 244 Pin Mini-DIMM
  - PCB – 30.00mm (1.181") TYP

DESCRIPTION

The WV3HG264M72EEU is a 2x64Mx72 Double Data Rate DDR2 SDRAM high density module. This memory module consists of eighteen 64Mx8 bit with 4 banks DDR2 Synchronous DRAMs in FBGA packages, mounted on a 244-pin DIMM FR4 substrate.

* This product is under development, is not qualified or characterized and is subject to change without notice.

NOTE: Consult factory for availability of:
- Vendor source control options
- Industrial temperature option

OPERATING FREQUENCIES

	PC2-3200	PC2-4200	PC2-5300*	PC2-6400*
Clock Speed	200MHz	266MHz	333MHz	400MHz
CL-t_{RCD}-t_{RP}	3-3-3	4-4-4	5-5-5	6-6-6

*Consult factory for availability.

PIN CONFIGURATION

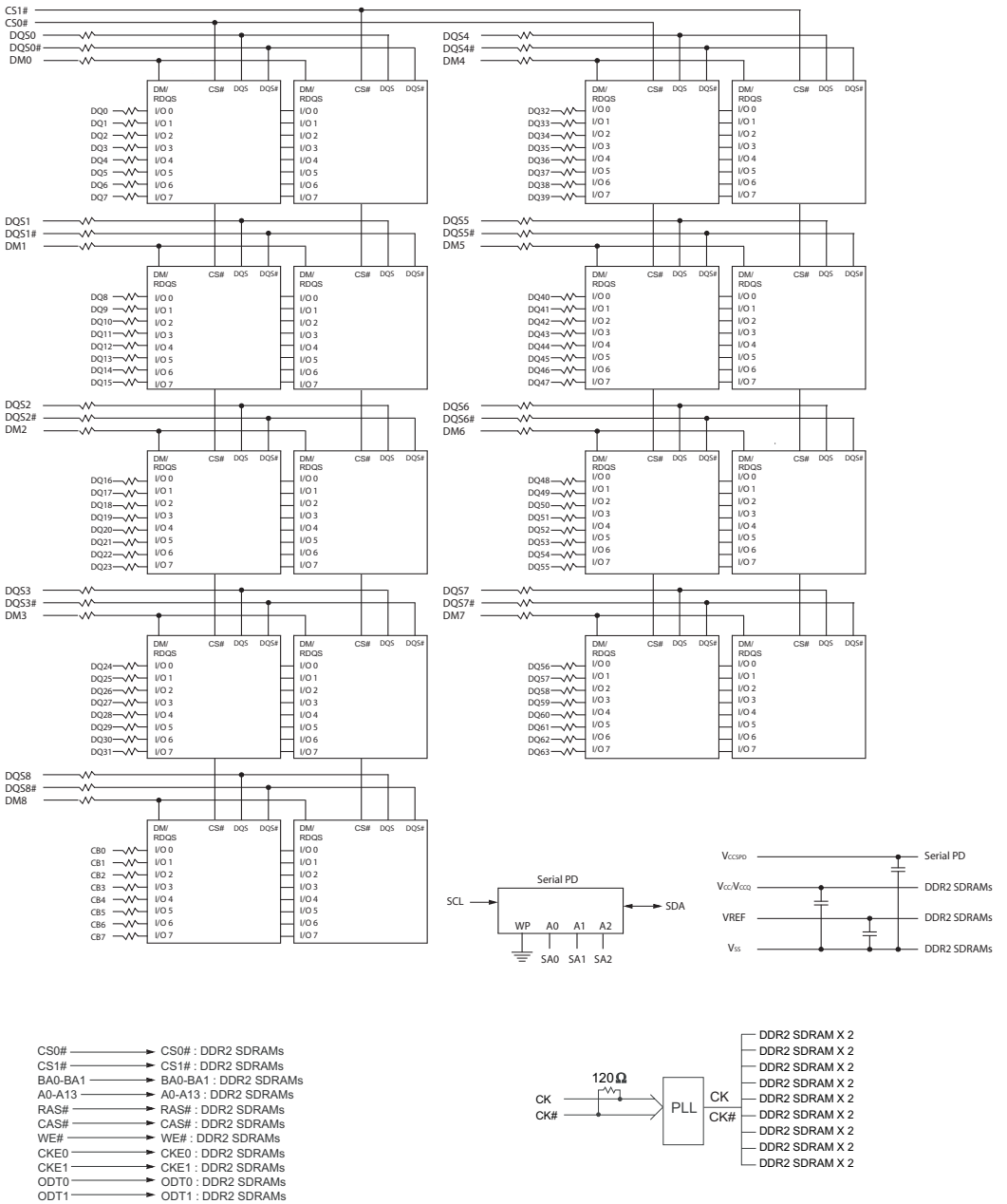
Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol
1	V_{REF}	62	A4	123	V_{SS}	184	V_{CCQ}
2	V_{SS}	63	V_{CCQ}	124	DQ4	185	A3
3	DQ0	64	A2	125	DQ5	186	A1
4	DQ1	65	V_{CC}	126	V_{SS}	187	V_{CC}
5	V_{SS}	66	V_{SS}	127	DM0	188	CK0
6	DQS0#	67	V_{SS}	128	NC	189	CK0#
7	DQS0	68	NC	129	V_{SS}	190	V_{CC}
8	V_{SS}	69	V_{CC}	130	DQ6	191	A0
9	DQ2	70	A10/AP	131	DQ7	192	BA1
10	DQ3	71	BA0	132	V_{SS}	193	V_{CC}
11	V_{SS}	72	V_{CC}	133	DQ12	194	RAS#
12	DQ8	73	WE#	134	DQ13	195	V_{CCQ}
13	DQ9	74	V_{CCQ}	135	V_{SS}	196	CS0#
14	V_{SS}	75	CAS#	136	DM1	197	V_{CCQ}
15	DQS1#	76	V_{CCQ}	137	NC	198	ODT0
16	DQS1	77	CS1#	138	V_{SS}	199	A13
17	V_{SS}	78	ODT1	139	NC	200	V_{CC}
18	NC	79	V_{CCQ}	140	NC	201	NC
19	NC	80	NC	141	V_{SS}	202	V_{SS}
20	V_{SS}	81	V_{SS}	142	DQ14	203	DQ36
21	DQ10	82	DQ32	143	DQ15	204	DQ37
22	DQ11	83	DQ33	144	V_{SS}	205	V_{SS}
23	V_{SS}	84	V_{SS}	145	DQ20	206	DM4
24	DQ16	85	DQS4#	146	DQ21	207	NC
25	DQ17	86	DQS4	147	V_{SS}	208	V_{SS}
26	V_{SS}	87	V_{SS}	148	DM2	209	DQ38
27	DQS2#	88	DQ34	149	NC	210	DQ39
28	DQS2	89	DQ35	150	V_{SS}	211	V_{SS}
29	V_{SS}	90	V_{SS}	151	DQ22	212	DQ44
30	DQ18	91	DQ40	152	DQ23	213	DQ45
31	DQ19	92	DQ41	153	V_{SS}	214	V_{SS}
32	V_{SS}	93	V_{SS}	154	DQ28	215	DM5
33	DQ24	94	DQS5#	155	DQ29	216	NC
34	DQ25	95	DQS5	156	V_{SS}	217	V_{SS}
35	V_{SS}	96	V_{SS}	157	DM3	218	DQ46
36	DQS3#	97	DQ42	158	NC	219	DQ47
37	DQS3	98	DQ43	159	V_{SS}	220	V_{SS}
38	V_{SS}	99	V_{SS}	160	DQ30	221	DQ52
39	DQ26	100	DQ48	161	DQ31	222	DQ53
40	DQ27	101	DQ49	162	V_{SS}	223	V_{SS}
41	V_{SS}	102	V_{SS}	163	CB4	224	NC
42	CB0	103	SA2	164	CB5	225	NC
43	CB1	104	NC	165	V_{SS}	226	V_{SS}
44	V_{SS}	105	V_{SS}	166	DM8	227	DM6
45	DQS8#	106	DQS6#	167	NC	228	NC
46	DQS8	107	DQS6	168	V_{SS}	229	V_{SS}
47	V_{SS}	108	V_{SS}	169	CB6	230	DQ54
48	CB2	109	DQ50	170	CB7	231	DQ55
49	CB3	110	DQ51	171	V_{SS}	232	V_{SS}
50	V_{SS}	111	V_{SS}	172	NC	233	DQ60
51	NC	112	DQ56	173	V_{CCQ}	234	DQ61
52	V_{CCQ}	113	DQ57	174	CKE1	235	V_{SS}
53	CKE0	114	V_{SS}	175	V_{CC}	236	DM7
54	V_{CC}	115	DQS7#	176	NC	237	NC
55	NC	116	DQS7	177	NC	238	V_{SS}
56	NC	117	V_{SS}	178	V_{CCQ}	239	DQ62
57	V_{CCQ}	118	DQ58	179	A12	240	DQ63
58	A11	119	DQ59	180	A9	241	V_{SS}
59	A7	120	V_{SS}	181	V_{CC}	242	SDA
60	V_{CC}	121	SA0	182	A8	243	SCL
61	A5	122	SA1	183	A6	244	V_{CCSPD}

RESET (pin 18) is connected to both OE of the PLL and Reset# of the register .

PIN NAMES

Pin Name	Function
A0-A13	Address Inputs
BA0,BA1	SDRAM Bank Address
DQ0-DQ63	Data Input/Output
CB0-CB7	Check Bits
DQS0-DQS8	Data strobes
DQS0#-DQS8#	Data strobes complement
ODT0, ODT1	On-die termination control
CK0,CK0#	Clock Inputs, positive line
CKE0, CKE1	Clock Enables
CS0#, CS1#	Chip Selects
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
DM (0-8)	Data Masks
V_{CCSPD}	SPD Power
V_{CC}	Voltage Supply
V_{CCQ}	I/O Power
V_{SS}	Ground
SA0-SA2	SPD address
SDA	SPD Data Input/Output
SCL	SPD Clock Input
V_{REF}	Input/Output Reference
NC	No connect

FUNCTIONAL BLOCK DIAGRAM



NOTE: All resistor values are 22 ohms ±5% unless otherwise specified.

DC OPERATING CONDITIONS

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Typical	Max	Unit	Notes
Supply Voltage	V_{CC}	1.7	1.8	1.9	V	3
I/O Reference Voltage	V_{REF}	0.49 x V_{CC}	0.50 x V_{CC}	0.51 x V_{CC}	V	1
I/O Termination Voltage	V_{TT}	V_{REF}-0.04	V_{REF}	V_{REF}+0.04	V	2
SPD Supply Voltage	V_{CCSPD}	1.7	-	3.6	V	

Notes:

1 V_{REF} is expected to equal $V_{CC/2}$ of the transmitting device and to track variations in the DC level of the same. Peak-to-peak noise on V_{REF} may not exceed +/-1 percent of the DC value. Peak-to-peak AC noise on V_{REF} may not exceed +/-2 percent of V_{REF}. This measurement is to be taken at the nearest V_{REF} bypass capacitor.

2. V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF} and must track variations in the DC level of V_{REF}.

3. V_{CCQ} of all IC's are tied to V_{CC}.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Min	Max	Units
V_{CC}	Voltage on V_{CC} pin relative to V_{SS}		-0.5	2.3	V
V_{IN}, V_{OUT}	Voltage on any pin relative to V_{SS}		-0.5	2.3	V
T_{STG}	Storage Temperature		-55	100	°C
I_L	Input leakage current; Any input 0V<V_{IN}<V_{CC}; V_{REF} input 0V,V_{IN},0.95V; Other pins not under test = 0V	Command/Address, RAS#, CAS#, WE#,	-90	90	µA
		CS#, CKE, ODT	-45	45	µA
		CK, CK#	-10	10	µA
		DM	-10	10	µA
I_{OZ}	Output leakage current; 0V<V_{IN}<V_{CC}; DQs and ODT are disable	DQ, DQS, DQS#	-10	10	µA
I_{VREF}	V_{REF} leakage current; V_{REF} = Valid V_{REF} level		-36	36	µA

INPUT/OUTPUT CAPACITANCE

TA=25 0 C, f=1 00MHz

Parameter	Symbol	Min	Max	Unit
Input capacitance (A0 - A13, BA0 - BA1 ,RAS#,CAS#,WE#)	C_{IN1}	22	40	pF
Input capacitance (CKE0, CKE1), (ODT0, ODT1)	C_{IN2}	13	22	pF
Input capacitance (CS0#, CS1#)	C_{IN3}	13	22	pF
Input capacitance (CK0, CK0#)	C_{IN4}	6	7	pF
Input capacitance (DM0 - DM8), (DQS0 - DQS8)	$C_{IN5\ (665)}$	9	11	pF
	$C_{IN5\ (534, 403)}$	9	12	pF
Input capacitance (DQ0 - DQ63), (CB0 - CB7)	$C_{OUT1\ (665)}$	9	11	pF
	$C_{OUT1\ (534, 403)}$	9	12	pF

OPERATING TEMPERATURE CONDITION

Parameter	Symbol	Rating	Units	Notes
Operating temperature (Commercial)	T_{OPER}	0°C to 85°C	°C	1, 2

Notes:
1. Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDEC JESD51 .2
2. At 0 - 85°C, operation temperature range, all DRAM specification will be supported.

INPUT DC LOGIC LEVEL

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Unit
Input High (Logic 1) Voltage	V_{IH}(DC)	V_{REF} + 0.125	V_{REF} + 0.300	V
Input Low (Logic 0) Voltage	V_{IL}(DC)	-0.300	V_{REF} - 0.125	V

INPUT AC LOGIC LEVEL

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Unit
AC Input High (Logic 1) Voltage DDR2-400 & DDR2-533	V_{IH}(AC)	V_{REF} + 0.250	—	V
AC Input High (Logic 1) Voltage DDR2-667	V_{IH}(AC)	V_{REF} + 0.200	—	V
AC Input Low (Logic 0) Voltage DDR2-400 & DDR2-533	V_{IL}(AC)	—	V_{REF} - 0.250	V
AC Input Low (Logic 1) Voltage DDR2-667	V_{IL}(AC)	—	V_{REF} - 0.200	V

DDR2 I_{CC} SPECIFICATIONS AND CONDITIONS

Includes DDR2 SDRAM components only; V_{CC} = +1.8V±0.1V

Symbol	Parameter	Condition		806	665	534	403	Unit
I_{CC0}*	Operating one bank active-precharge;	$t_{CK} = t_{CK(I_{CC})}$; $t_{RC} = t_{RC(I_{CC})}$; $t_{RAS} = t_{RAS\ MIN(I_{CC})}$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	1,337	1,292	1,292	mA
I_{CC1}*	Operating one bank active-read-precharge;	I_{OUT} = 0mA; BL = 4; CL = CL(I_{CC}); $t_{CK} = t_{CK(I_{CC})}$; $t_{RC} = t_{RC(I_{CC})}$; $t_{RAS} = t_{RAS\ MIN(I_{CC})}$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING; Data pattern is same as I_{CC4W}.		TBD	1,272	1,227	1,227	mA
I_{CC2P}**	Precharge power-down current;	All banks idle; $t_{CK} = t_{CK(I_{CC})}$; CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING		TBD	444	444	444	mA
I_{CC2Q}**	Precharge quite standby current;	All banks idle; $t_{CK} = t_{CK(I_{CC})}$; CKE is HIGH; CS# is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING		TBD	930	840	840	mA
I_{CC2N}**	Precharge standby current;	All banks idle; $t_{CK} = t_{CK(I_{CC})}$; CKE is HIGH; CS# is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are SWITCHING		TBD	1,020	930	930	mA
I_{CC3P}**	Active power-down current;	All banks open; $t_{CK} = t_{CK(I_{CC})}$, CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	Fast PDN Exit MRS(12) = 0	TBD	840	840	840	mA
			Slow PDN Exit MRS(12) = 1	TBD	516	516	516	mA
I_{CC3N}**	Active standby current;	All banks open; $t_{CK} = t_{CK(I_{CC})}$; $t_{RC} = t_{RC(I_{CC})}$; $t_{RAS} = t_{RAS\ MIN(I_{CC})}$; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	1,290	1,200	1,200	mA
I_{CC4W}*	Operating burst write current;	All banks open; Continuous burst writes; BL = 4; CL = CL(I_{CC}); AL = 0; $t_{CK} = t_{CK(I_{CC})}$; $t_{RC} = t_{RC(I_{CC})}$; $t_{RAS} = t_{RAS\ MIN(I_{CC})}$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	1,632	1,452	1,362	mA
I_{CC4R}*	Operating burst read current;	All banks open; Continuous burst reads; TOUT = 0mA; BL = 4; CL = CL(I_{CC}); AL = 0; $t_{CK} = t_{CK(I_{CC})}$; $t_{RC} = t_{RC(I_{CC})}$; $t_{RAS} = t_{RAS\ MIN(I_{CC})}$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I_{CC4W}.		TBD	1,677	1,497	1,362	mA
I_{CC5}**	Burst auto refresh current;	$t_{CK} = t_{CK(I_{CC})}$; Refresh command at every $t_{RC(I_{CC})}$ interval; CKE is HIGH; CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	3,000	2,820	2,820	mA
I_{CC6}**	Self refresh current;	CK and CK# at 0V; CKE < 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING	Normal	TBD	144	144	144	mA
I_{CC7}*	Operating bank interleave read current;	All bank interleaving reads; I_{OUT} = 0mA; BL = 4; CL = CL(I_{CC}); AL = $t_{RCD(I_{CC})}$ - 1*$t_{CK(I_{CC})}$; $t_{CK} = t_{CK(I_{CC})}$; $t_{RC} = t_{RC(I_{CC})}$; $t_{RRD} = t_{RRD\ MIN(I_{CC})}$ = 1*$t_{CK(I_{CC})}$; CKE is HIGH; CS# is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data bus inputs are SWITCHING		TBD	2,352	2,352	2,352	mA

Notes:

I_{CC} specification is based on **SAMSUNG** components. Other DRAM manufacturers specification may be different.

* Value calculated as one module rank in this operating condition, and all other module ranks in I_{CC2P} (CKE LOW) mode.

** Value calculated reflects all module ranks in this operating condition.

AC TIMING PARAMETERS

V_{CC} = +1.8V ± 0.1V

Parameter			Symbol	806		665		534		403		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
Clock	Clock cycle time	CL=6	$t_{CK}(6)$	TBD	TBD							
		CL=5	$t_{CK}(5)$	TBD	TBD	3000	8000	-	-	-	-	ps
		CL=4	$t_{CK}(4)$	TBD	TBD	3750	8000	3,750	8,000	5,000	8,000	ps
		CL=3	$t_{CK}(3)$	TBD	TBD	5000	8000	5,000	8,000	5,000	8,000	ps
	CK high-level width		t_{CH}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}
	CK low-level width		t_{CL}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}
	Half clock period		t_{HP}	TBD	TBD	MIN(t_{CH}, t_{CL})		MIN (t_{CH}, t_{CL})		MIN (t_{CH}, t_{CL})		ps
	Clock jitter		t_{JIT}	TBD	TBD	-125	125	-125	125	-125	125	ps
Data	DQ output access time from CK/CK#		t_{AC}	TBD	TBD	-450	+450	-500	+500	-600	+600	ps
	Data-out high impedance window from CK/CK#		t_{HZ}	TBD	TBD		$t_{AC(MAX)}$		$t_{AC(MAX)}$		$t_{AC(MAX)}$	ps
	Data-out low-impedance window from CK/CK#		t_{LZ}	TBD	TBD	$t_{AC(MIN)}$	$t_{AC(MAX)}$	$t_{AC(MIN)}$	$t_{AC(MAX)}$	$t_{AC(MIN)}$	$t_{AC(MAX)}$	ps
	DQ and DM input setup time relative to DQS		t_{DS}	TBD	TBD	100		100		150		
	DQ and DM input hold time relative to DQS		t_{DH}	TBD	TBD	175		225		275		
	DQ and DM input pulse width (for each input)		t_{DIPW}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	Data hold skew factor		t_{QHS}	TBD	TBD		340		400		450	ps
	DQ-DQS hold, DQS to first DQ to go nonvalid, per access		t_{QH}	TBD	TBD	t_{HP} - t_{QHS}		t_{HP} - t_{QHS}		t_{HP} - t_{QHS}		ps
	Data valid output window (DVW)		t_{DVW}	TBD	TBD	t_{QH} - t_{DQSQ}		t_{QH} - t_{DQSQ}		t_{QH} - t_{DQSQ}		ns
Data Strobe	DQS input high pulse width		t_{DQSH}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	DQS input low pulse width		t_{DQSL}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	DQS output access time from CK/CK#		t_{DQSCK}	TBD	TBD	-400	+400	-450	+450	-500	+500	ps
	DQS falling edge to CK rising - setup time		t_{DSS}	TBD	TBD	0.2		0.2		0.2		t_{CK}
	DQS falling edge from CK rising - hold time		t_{DSH}	TBD	TBD	0.2		0.2		0.2		t_{CK}
	DQS-DQ skew, DOS to last DQ valid, per group, per access		t_{DQSQ}	TBD	TBD		240		300		350	ps
	DQS read preamble		t_{RPRE}	TBD	TBD	0.9	1.1	0.9	1.1	0.9	1.1	t_{CK}
	DQS read postamble		t_{RPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t_{CK}
	DQS write preamble setup time		t_{WPRES}	TBD	TBD	0		0		0		ps
	DQS write preamble		t_{WPRE}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	DQS write postamble		t_{WPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t_{CK}
	Write command to first DQS latching transition		t_{DQSS}	TBD	TBD	WL-0.25	WL+0.25	WL-0.25	WL+0.25	WL-0.25	WL+0.25	t_{CK}

AC specification is based on **SAMSUNG** components. Other DRAM manufacturers specification may be different.

AC TIMING PARAMETERS (continued)

V_{CC} = +1.8V ± 0.1V

Parameter		Symbol	806		665		534		403		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
Command and Address	Address and control input pulse width for each input	t_{IPW}	TBD	TBD	0.6		0.6		0.6		t_{CK}
	Address and control input setup time	t_{IS}	TBD	TBD	200		250		250		ps
	Address and control input hold time	t_{IH}	TBD	TBD	275		375		475		ps
	CAS# to CAS# command delay	t_{CCD}	TBD	TBD	2		2		2		ps
	ACTIVE to ACTIVE (same bank) command	t_{RC}	TBD	TBD	54		55		55		ns
	ACTIVE bank a to ACTIVE bank b command	t_{RRD}	TBD	TBD	7.5		7.5		7.5		ns
	ACTIVE to READ or WRITE delay	t_{RCD}	TBD	TBD	15		15		15		ns
	Four Bank Activate period	t_{FAW}	TBD	TBD	37.5	37.5	37.5	37.5	37.5	37.5	ns
	ACTIVE to PRECHARGE command	t_{RAS}	TBD	TBD	45	70,000	45	70,000	45	70,000	ns
	Internal READ to precharge command delay	t_{RTP}	TBD	TBD	7.5		7.5		7.5		ns
	Write recovery time	t_{WR}	TBD	TBD	15		15		15		ns
	Auto precharge write recovery + precharge time	t_{DAL}	TBD	TBD	$t_{WR} + t_{RP}$		$t_{WR} + t_{RP}$		$t_{WR} + t_{RP}$		ns
	Internal WRITE to READ command delay	t_{WTR}	TBD	TBD	7.5		7.5		10		ns
	PRECHARGE command period	t_{RP}	TBD	TBD	15		15		15		ns
	PRECHARGE ALL command period	t_{RPA}	TBD	TBD	$t_{RP} + t_{CK}$		$t_{RP} + t_{CK}$		$t_{RP} + t_{CK}$		ns
	LOAD MODE command cycle time	t_{MRD}	TBD	TBD	2		2		2		t_{CK}
	CKE low to CK, CK# uncertainty	t_{DELAY}	TBD	TBD	$t_{IS}+t_{CK}+t_{IH}$		$t_{IS}+t_{CK}+t_{IH}$		$t_{IS}+t_{CK}+t_{IH}$		ns
Self Refresh	REFRESH to Active or Refresh to Refresh command interval	t_{RFC}	TBD	TBD	105	70,000	105	70,000	105	70,000	ns
	Average periodic refresh interval	t_{REFI}	TBD	TBD		7.8		7.8		7.8	ns
	Exit self refresh to non-READ command	t_{XSNR}	TBD	TBD	$t_{RFC(MIN)}$ + 10		$t_{RFC(MIN)}$ + 10		$t_{RFC(MIN)}$ + 10		ns
	Exit self refresh to READ	t_{XSRD}	TBD	TBD	200		200		200		t_{CK}
	Exit self refresh timing reference	t_{ISXR}	TBD	TBD	t_{IS}		t_{IS}		t_{IS}		ps
ODT	ODT turn-on delay	t_{AOND}	TBD	TBD	2	2	2	2	2	2	t_{CK}
	ODT turn-on	t_{ACN}	TBD	TBD	$t_{AC(MIN)}$	$t_{AC(MAX)}$ + 1000	$t_{AC(MIN)}$	$t_{AC(MAX)}$ + 1000	$t_{AC(MIN)}$	$t_{AC(MAX)}$ + 1000	ps
	ODT turn-off delay	t_{AOFD}	TBD	TBD	2.5	2.5	2.5	2.5	2.5	2.5	t_{CK}
	ODT turn-off	t_{AOF}	TBD	TBD	$t_{AC(MIN)}$	$t_{AC(MAX)}$ + 600	$t_{AC(MIN)}$	$t_{AC(MAX)}$ + 600	$t_{AC(MIN)}$	$t_{AC(MAX)}$ + 600	ps
	ODT turn-on (power-down mode)	t_{AONPD}	TBD	TBD	$t_{AC(MIN)}$ + 2000	2 x t_{CK} + $t_{AC(MAX)}$ + 1000	$t_{AC(MIN)}$ + 2000	2 x t_{CK} + $t_{AC(MAX)}$ + 1000	$t_{AC(MIN)}$ + 2000	2 x t_{CK} + $t_{AC(MAX)}$ + 1000	ps
	ODT turn-off (power-down mode)	t_{AOFPD}	TBD	TBD	$t_{AC(MIN)}$ + 2000	2 x t_{CK} + $t_{AC(MAX)}$ + 1000 +1000	$t_{AC(MIN)}$ + 2000	2 x t_{CK} + $t_{AC(MAX)}$ + 1000 +1000	$t_{AC(MIN)}$ + 2000	2 x t_{CK} + $t_{AC(MAX)}$ + 1000	ps
	ODT to power-down entry latency	t_{ANPD}	TBD	TBD	3		3		3		t_{CK}
	ODT power-down exit latency	t_{AXPD}	TBD	TBD	8		8		8		t_{CK}
Power-Down	Exit active power-down to READ command, MR[bit12=0]	t_{XARD}	TBD	TBD	2		2		2		t_{CK}
	Exit active power-down to READ command, MR[bit12=1]	t_{XARDS}	TBD	TBD	7-AL		6-AL		6-AL		t_{CK}
	Exit precharge power-down to any non-READ command	t_{XP}	TBD	TBD	2		2		2		t_{CK}
	CKE minimum high/low time	t_{CKE}	TBD	TBD	3		3		3		t_{CK}

AC specification is based on **SAMSUNG** components. Other DRAM manufacturers specification may be different.

ORDERING INFORMATION FOR D7

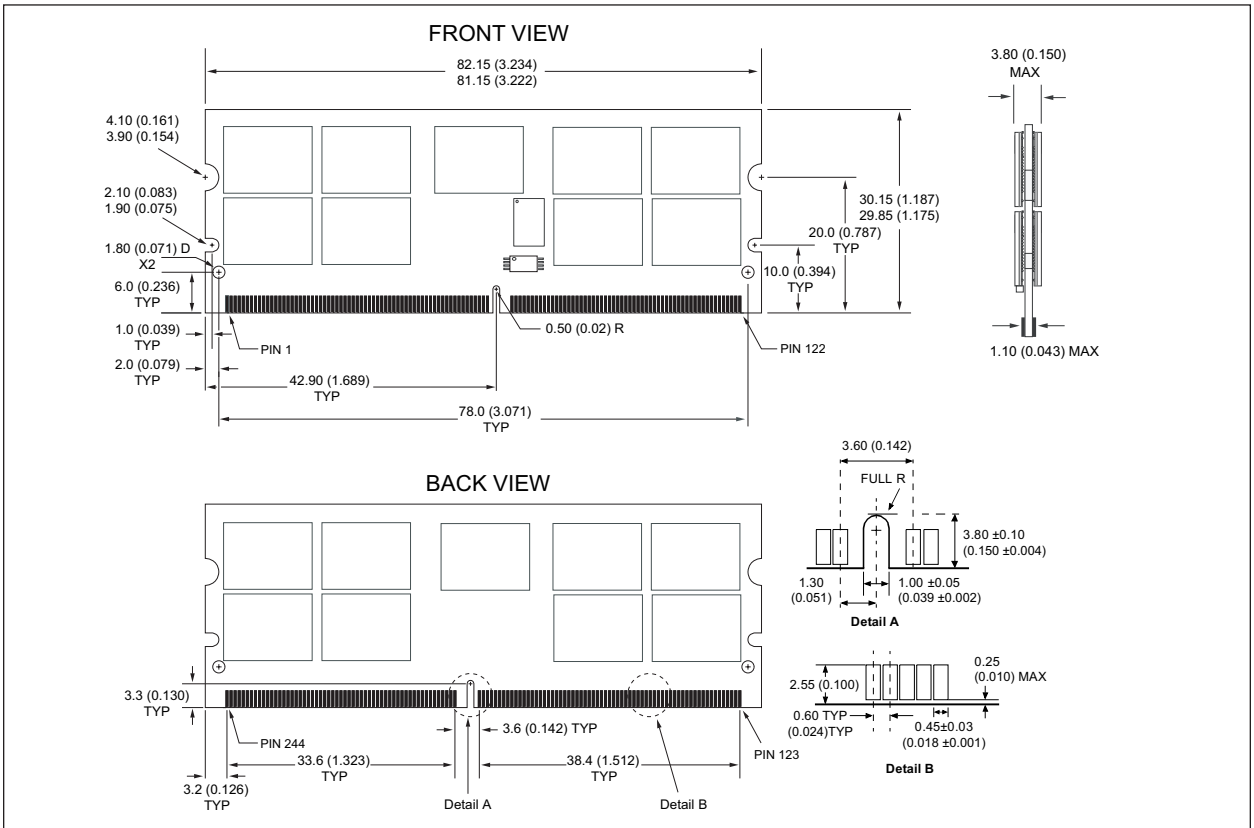
Part Number	Clock Speed/ Data Rate	CAS Latency	t_{RCD}	t_{RP}	Height*
WV3HG264M72EEU806D7xxG**	400MHz/800Mb/s	6	6	6	30.00mm (1.181") TYP
WV3HG264M72EEU665D7xxG**	333MHz/667Mb/s	5	5	5	30.00mm (1.181") TYP
WV3HG264M72EEU534D7xxG	266MHz/533Mb/s	4	4	4	30.00mm (1.181") TYP
WV3HG264M72EEU403D7xG	200MHz/400Mb/s	3	3	3	30.00mm (1.181") TYP

** Contact factory for availability.

NOTES:

- RoHS product. ("G" = RoHS Compliant)
- Vendor specific part numbers are used to provide memory components source control. The place holder for this is shown as lower case"x" in the part numbers above and is to be replaced with the respective vendors code. Consult factory for qualified sourcing options. (M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

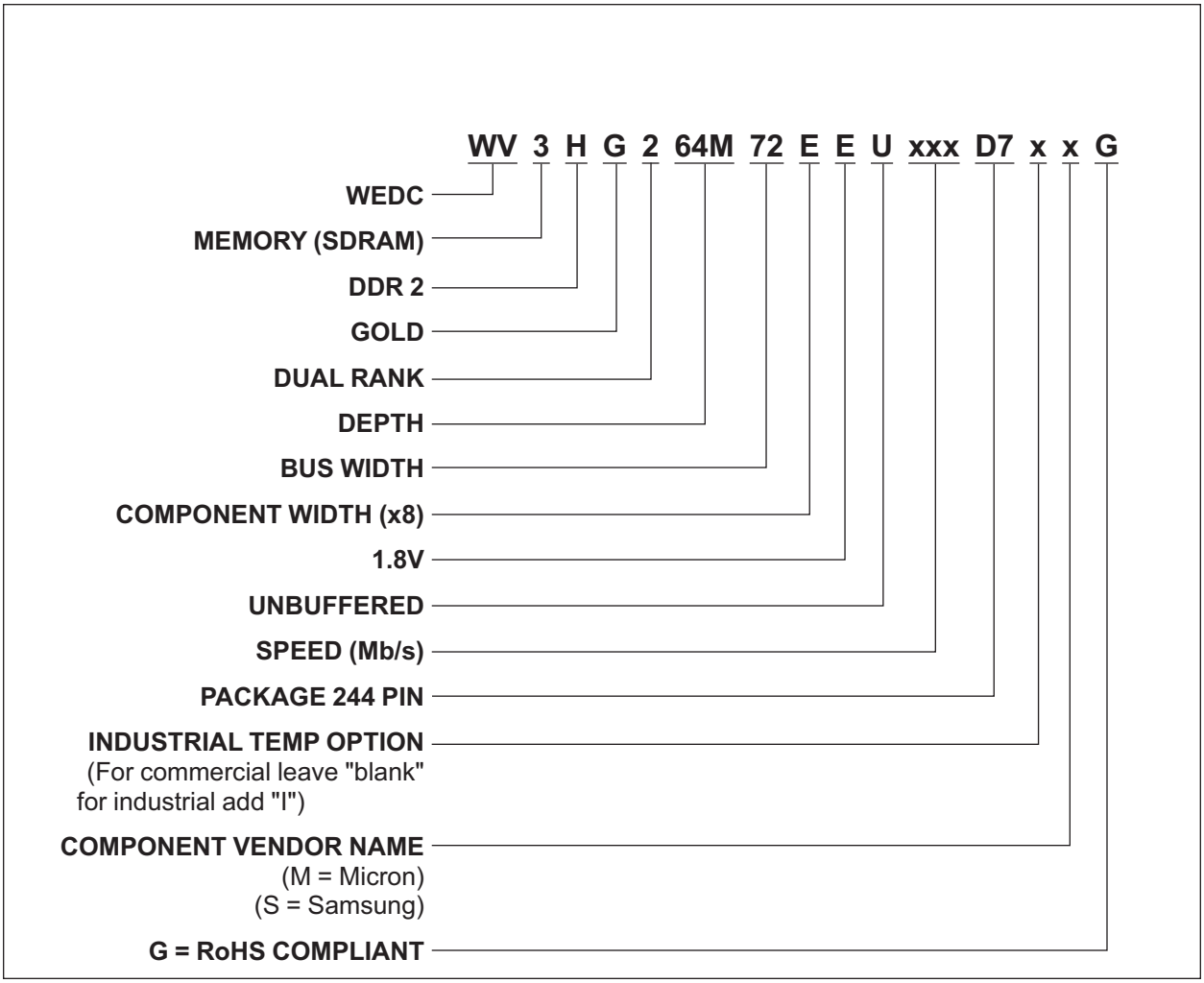
PACKAGE DIMENSIONS FOR D7



Tolerances: + /- 0.13 (0.005) unless otherwise specified.

* ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES)

PART NUMBERING GUIDE



Document Title

1GB – 2x64Mx72 DDR2 SDRAM UNBUFFERED, w/PLL, Mini-DIMM

DRAM DIE OPTIONS:

- SAMSUNG: C-Die, will move to E-Die Q2'06
- MICRON: U37Y: B-Die

Revision History

Rev #	History	Release Date	Status
Rev 0	Created	May 2006	Advanced